# 2SB0953 (2SB953), 2SB0953A (2SB953A)

# Silicon PNP epitaxial planar type

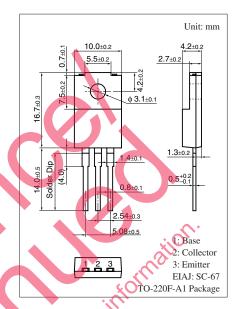
For low-voltage switching

#### ■ Features

- Low collector-emitter saturation voltage V<sub>CE(sat)</sub>
- High-speed switching
- Full-pack package which can be installed to the heat sink with one screw

## ■ Absolute Maximum Ratings $T_C = 25$ °C

Parameter	Symbol	Rating	Unit	
Collector-base voltage	2SB0953	V <sub>CBO</sub>	-40	V
(Emitter open)	2SB0953A		-50	
Collector-emitter voltage	2SB0953	V <sub>CEO</sub>	-20	V
(Base open)	2SB0953A		-40	
Emitter-base voltage (Collector open)		V <sub>EBO</sub>	-5	V
Collector current	$I_C$	-7	A	
Peak collector current	$I_{CP}$	-12	A	
Collector power		P <sub>C</sub>	30	W
dissipation	$T_a = 25^{\circ}C$		2	
Junction temperature		$T_{j}$	150	°C
Storage temperature		$T_{stg}$	-55 to +1 <b>50</b>	°C



■ Electrical Characteristics  $T_C = 25^{\circ}C \pm 3^{\circ}C$ 

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Collector-emitter voltage 2SB0953	V <sub>CEO</sub>	$I_C = -10 \text{ mA}, I_B = 0$	-20			V
(Base open) 2SB0953A		71, 201,	-40			
Collector-base cutoff 2SB0953	$I_{CBO}$	$V_{\rm CB} = -40 \text{ V.} I_{\rm E} = 0$			-50	μΑ
current (Emitter open) 2SB0953A		$V_{CB} = -50 \text{ W}, I_E = 0$			-50	
Emitter-base cutoff current (Collector open)	$I_{EBO}$	$V_{EB} = -5 \text{ V}, I_C = 0$			-50	μΑ
Forward current transfer ratio	h <sub>FE1</sub>	$V_{CE} = -2 V$ , $I_{C} = -0.1 A$	45			_
	h <sub>FE2</sub> *	$V_{CE} = -2 V, I_C = -2 A$	60		260	
Collector-emitter saturation voltage	V <sub>CE(sat)</sub>	$I_C = -5 \text{ A}, I_B = -0.16 \text{ A}$			- 0.6	V
Base-emitter saturation voltage	V <sub>BE(sat)</sub>	$I_C = -5 A, I_B = -0.16 A$			-1.5	V
Transition frequency	$f_T$	$V_{CE} = -10 \text{ V}, I_C = -0.5 \text{ A}, f = 10 \text{ MHz}$		150		MHz
Collector output capacitance	C <sub>ob</sub>	$V_{CB} = -10 \text{ V}, I_E = 0, f = 1 \text{ MHz}$		140		pF
(Common base, input open circuited)						
Turn-on time	t <sub>on</sub>	$I_C = -2 \text{ A}, I_{B1} = -66 \text{ mA}, I_{B2} = 66 \text{ mA}$		0.1		μs
Storage time	t <sub>stg</sub>	$V_{CC} = -20 \text{ V}$		0.5		μs
Fall time	$t_{\rm f}$			0.1		μs

Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

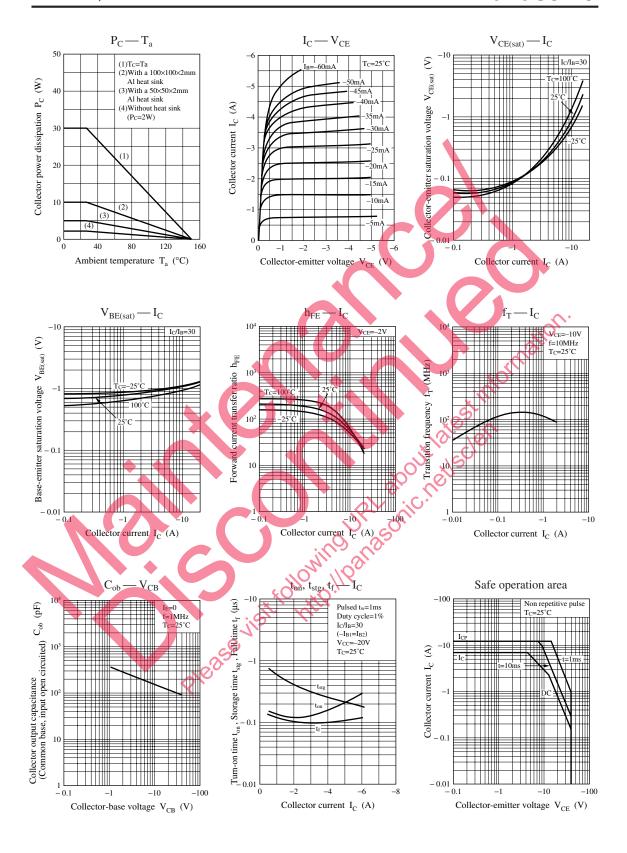
#### 2. \*: Rank classification

Rank	R	Q	Р	
h <sub>FE2</sub>	60 to 120	90 to 180	130 to 260	

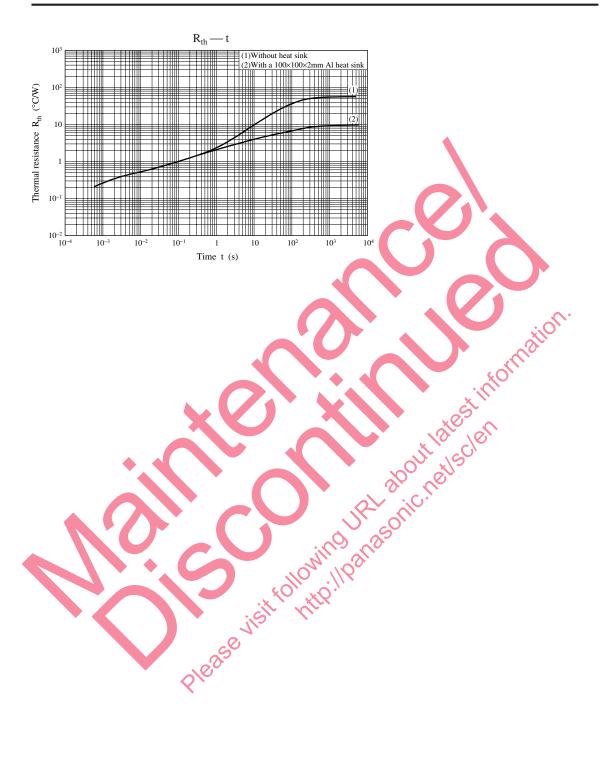
Note) The part numbers in the parenthesis show conventional part number.

Publication date: April 2003 SJD00032BED 1

# **Panasonic**



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